

ABSTRACT

A susceptor (2) in which a semiconductor substrate (W) is supported approximately horizontally in a pocket (2c) when performing a vapor phase growth of a single crystal thin film on a front surface of the semiconductor substrate (W), and in which the pocket (2c) comprises an outer peripheral pocket portion (20) to support the semiconductor substrate (W) and a central side pocket portion (21) which is formed inside the outer peripheral side pocket portion (20) to be concave from the outer peripheral side pocket portion (20), wherein the outer peripheral side pocket portion (20) comprises a substrate supporting surface (20a) which is inclined with respect to a horizontal surface to be lowered toward a central side from an outer peripheral side of the pocket (2c), and a region of the substrate supporting surface (20a) excluding at least an inner peripheral edge supports a portion of a rear surface of the semiconductor substrate (W) which is inside an outer peripheral edge of the semiconductor substrate (W).